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Author index

Ansell, B.J., see Xu, H.Z. 218 (2000) 1
Aoki, M., H. Yamane, M. Shimada, T. Sekiguchi, T. Hanada, T. Yao, S. Sarayama and F.J. DiSalvo, Growth of GaN single crystals from a Na–Ga melt at 750°C and 5 MPa of N_2 218 (2000) 7
Arnold, C.M., see Ji, D. 218 (2000) 390

Ballarotto, V.W., M.E. Little and M.E. Kordesch, Orientation of aluminum nitride films grown with hyperthermal molecular beams 218 (2000) 173
Batail, P., see Molas, S. 218 (2000) 399
Beadle, E., see Ji, D. 218 (2000) 390
Beaumont, B., see Frayssinet, E. 218 (2000) 161
Beňačka Š., see Španková, M. 218 (2000) 287
Benamara, M., Z. Liliental-Weber, S. Kellermann, W. Swider, J. Washburn, J. Mazur and E.D. Bourret-Courchesne, Study of high quality GaN grown by OMVPE using an intermediate layer 218 (2000) 447
Benson, R., see Ji, D. 218 (2000) 390
Billia, B., see Drevet, B. 218 (2000) 419
Bourgoin, J.C., see Gandouzi, M. 218 (2000) 167
Bourret-Courchesne, E.D., see Benamara, M. 218 (2000) 447
Brandt, O., see Waltereit, P. 218 (2000) 143

Camel, D., see Drevet, B. 218 (2000) 419
Caro, J., see Molas, S. 218 (2000) 399
Chen, H., see Liu, H.F. 218 (2000) 191
Chen, W.Z., see Zhang, D.Y. 218 (2000) 98
Chen, X.H., H.S. Yang, G.T. Wu, M. Wang, F.M. Deng, X.B. Zhang, J.C. Peng and W.Z. Li, Generation of curved or closed-shell carbon nanostructures by ball-milling of graphite 218 (2000) 57
Chen, Xiumei, Qiang Wang and Kunquar Lu, Temperature dependence of viscosity of molten lithium niobate 218 (2000) 93
Chen, Y., see Sun, Z. 218 (2000) 203
Cheng Buwen, see Yu Zhuo 218 (2000) 245
Cheng, M. and S. Kou, Detecting temperature oscillation in a silicon liquid bridge 218 (2000) 132
Cheng, R., see Zhang, H. 218 (2000) 81
Cheng, Y.S., see Kuršumović, A. 218 (2000) 45
Cheong, W.S., D.Y. Yoon, D.-Y. Kim and N.M. Hwang, Effect of substrates on morphological evolution of a film in the silicon CVD process: approach by charged cluster model 218 (2000) 27
Cheong, W.S., see Hwang, N.M. 218 (2000) 33
Chernov, A.A., see Murray, B.T. 218 (2000) 434
Chian, J.H., see Lan, C.W. 218 (2000) 115
Cho, S.H., see Shen, X.Q. 218 (2000) 155
Choe, K.S. and B.N. Jang, Minority-carrier lifetime optimization in silicon MOS devices by intrinsic gettering 218 (2000) 239
Choh, S.H., see Koh, E. 218 (2000) 214
Chromik, Š., see Španková, M. 218 (2000) 287
Colorado Jr., R., see Ji, D. 218 (2000) 390
Coriell, S.R., see Murray, B.T. 218 (2000) 434
Crone, W.C., Compositional variation and precipitate structures of copper–beryllium single crystals grown by the Bridgman technique 218 (2000) 381
Cui, J.-J., see Yin, L.-W. 218 (2000) 455

Dalas, E., see Koutsopoulos, S. 218 (2000) 353
Dalas, E., see Manoli, F. 218 (2000) 359
Dawes, J., see Zhang, H. 218 (2000) 81
Deng, F.M., see Chen, X.H. 218 (2000) 57
Deng, P., see Yang, P. 218 (2000) 87
DiSalvo, F.J., see Aoki, M. 218 (2000) 7
Ding, D., see Sun, Z. 218 (2000) 203
Ding, D., see Li, Y.F. 218 (2000) 451
Dong, C., see Zhang, H. 218 (2000) 81
Dong, G.S., see Qian, D. 218 (2000) 197
Dovlitova, L., see Isaenko, L. 218 (2000) 313
Drevet, B., H. Nguyen Thi, D. Camel, B. Billia and M.D. Dupouy, Solidification of aluminium–lithium alloys near the cell/dendrite transition-influence of solutal convection 218 (2000) 419

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PII: S0022-0248(00)00678-3

Dumpich, G., see Müller, Ch. 218 (2000) 410
Dunn, R.V., see Ji, D. 218 (2000) 390
Dupouy, M.D., see Drevet, B. 218 (2000) 419
Durbin, S.D., see Yoshikawa, A. 218 (2000) 67

Eguchi, M., see Ma, M. 218 (2000) 232
Eisenmenger-Sittner, C., Diffusion mediated film growth on polycrystalline substrates 218 (2000) 103
Epelbaum, B.M., see Yoshikawa, A. 218 (2000) 67
Evetts, J.E., see Kuršumović, A. 218 (2000) 45

Feng, J.Y., see Liu, J.F. 218 (2000) 272
Feng, S.L., see Wang, X.D. 218 (2000) 209
Ferhat, M., J.C. Tedenac and J. Nagao, Mechanisms of spiral growth in Bi_2Te_3 thin films grown by the hot-wall-epitaxy technique 218 (2000) 250
Figueras, A., see Molas, S. 218 (2000) 399
Földvári, I., see Polgár, K. 218 (2000) 327
Fourmigué, M., see Molas, S. 218 (2000) 399
Foxon, C.T., see Xu, H.Z. 218 (2000) 1
Fraxedas, J., see Molas, S. 218 (2000) 399
Frayssinet, E., W. Knap, P. Prystawko, M. Leszczynski, I. Grzegory, T. Suski, B. Beaumont and P. Gibart, Infrared studies on GaN single crystals and homoepitaxial layers 218 (2000) 161
Fröhlich, K., see Španková, M. 218 (2000) 287
Friedman, J.M., see Ji, D. 218 (2000) 390
Friedrich, J., see Nicoara, I. 218 (2000) 74
Fukuda, T., see Yoshikawa, A. 218 (2000) 67

Gandouzi, M., J.C. Bourgoin, J. Mimila-Arroyo, Cl. Grattepain and Ch. Grattepain, Impurity incorporation during epitaxial growth of GaAs by chemical reaction 218 (2000) 167
Gaži, Š., see Španková, M. 218 (2000) 287
Ge, Weikun, see Lu, Liwu 218 (2000) 13
Gibart, P., see Frayssinet, E. 218 (2000) 161
Glowacki, B.A., see Kuršumović, A. 218 (2000) 45
Goriletsky, V.I. and N.N. Smirnov, The specifics of crystal growing in non-conservative systems 218 (2000) 125
Grattepain, Ch., see Gandouzi, M. 218 (2000) 167
Grattepain, Cl., see Gandouzi, M. 218 (2000) 167
Graupe, M., see Ji, D. 218 (2000) 390
Grzegory, I., see Frayssinet, E. 218 (2000) 161

Han, Y.J., see Liu, H.F. 218 (2000) 191
Hanada, T., see Aoki, M. 218 (2000) 7
Hao, Z.-Y., see Yin, L.-W. 218 (2000) 455
Hara, S., see Shen, X.Q. 218 (2000) 155
Harrison, I., see Xu, H.Z. 218 (2000) 1
Hasegawa, K., see Yoshikawa, A. 218 (2000) 67
Hatta, A., see Jiang, N. 218 (2000) 265
He, J. and S. Kou, Erratum to "LEC growth of In-doped GaAs with bottom solid feeding". [J. Crystal Growth 216 (2000) 21–25] 218 (2000) 140
Hellemans, L., see Španková, M. 218 (2000) 287
Higuchi, M., H. Katase, K. Kodaira and S. Nakayama, Float zone growth and characterization of $Pr_{9.33}(SiO_4)_6O_2$ and $Sm_{9.33}(SiO_4)_6O_2$ single crystals with an apatite structure 218 (2000) 282
Hiraki, A., see Jiang, N. 218 (2000) 265
Hong, K.J., T.S. Jeong, C.J. Yoon and Y.J. Shin, The optical properties of CdS crystal grown by the sublimation method 218 (2000) 19
Huang Changjun, see Yu Zhuo 218 (2000) 245
Huang, C.H., see Zhang, D.Y. 218 (2000) 98
Huang, Q., see Liu, H.F. 218 (2000) 191
Hwang, N.M., see Cheong, W.S. 218 (2000) 27
Hwang, N.M., W.S. Cheong, D.Y. Yoon and D.-Y. Kim, Growth of silicon nanowires by chemical vapor deposition: approach by charged cluster model 218 (2000) 33
Hwang, N.M. and D.-Y. Kim, Low-pressure synthesis of diamond without hydrogen: approach by charged cluster model 218 (2000) 40

Ide, T., see Shen, X.Q. 218 (2000) 155
Inaoka, T., see Wang, H.X. 218 (2000) 148
Inaoka, T., see Jiang, N. 218 (2000) 265
Irisawa, T., see Ma, M. 218 (2000) 232
Isaenko, L., I. Vasilyeva, A. Yelisseyev, S. Lobanov, V. Malakhov, L. Dovlitova, J.-J. Zondy and I. Kavun, Growth and characterization of $LiInS_2$ single crystals 218 (2000) 313
Ito, A., see Kaito, C. 218 (2000) 259

Jang, B.N., see Choe, K.S. 218 (2000) 239
Jayavel, R., see Ushasree, P.M. 218 (2000) 365
Jeong, J.H. and I.S. Kang, Analytical studies on the crystal–melt interface shape in the Czochralski process for oxide single crystals 218 (2000) 294
Jeong, T.S., see Hong, K.J. 218 (2000) 19
Ji, D., C.M. Arnold, M. Graupe, E. Beadle, R.V. Dunn, M.N. Phan, R.J. Villazana, R. Benson, R. Colorado Jr., T.J. Lee and J.M. Friedman, Improved protein crystallization by vapor diffusion from drops in contact with transparent, self-assembled monolayers on gold-coated glass coverslips 218 (2000) 390
Jia, X., A. Miyazaki and H. Kimura, Containerless processing using floating zone technique on the ground 218 (2000) 459
Jiang, N., S. Kujime, I. Ota, T. Inaoka, Y. Shintani, H. Makita, A. Hatta and A. Hiraki, Growth and structural analysis of nano-diamond films deposited on Si substrates pretreated by various methods 218 (2000) 265

Jiang, W.H., see Li, Y.F. 218 (2000) 451
Jin, X.F., see Qian, D. 218 (2000) 197

Kaito, C., A. Ito, S. Kimura, Y. Kimura, Y. Saito and T. Nakada, Topotactical growth of indium sulfide by evaporation of metal onto molybdenite 218 (2000) 259
Kang, I.S., see Jeong, J.H. 218 (2000) 294
Kashiwazaki, S., see Ohmura, R. 218 (2000) 372
Katase, H., see Higuchi, M. 218 (2000) 282
Kavun, I., see Isaenko, L. 218 (2000) 313
Kawabe, M., see Xu, H.Z. 218 (2000) 1
Kellermann, S., see Benamara, M. 218 (2000) 447
Kim, D.-Y., see Cheong, W.S. 218 (2000) 27
Kim, D.-Y., see Hwang, N.M. 218 (2000) 33
Kim, D.-Y., see Hwang, N.M. 218 (2000) 40
Kim, E.K., see Koh, E. 218 (2000) 214
Kimura, H., see Jia, X. 218 (2000) 459
Kimura, S., see Kaito, C. 218 (2000) 259
Kimura, Y., see Kaito, C. 218 (2000) 259
Klouras, N., see Koutsopoulos, S. 218 (2000) 353
Knap, W., see Frayssinet, E. 218 (2000) 161
Kodaira, K., see Higuchi, M. 218 (2000) 282
Koh, E.K., Y.J. Park, E.K. Kim, C.S. Park, S.H. Lee, J.H. Lee and S.H. Choh, The effect of N^+-implanted Si(1 1 1) substrate and buffer layer on GaN films 218 (2000) 214
Komatsu, F., see Wang, H.X. 218 (2000) 148
Kordesch, M.E., see Ballarotto, V.W. 218 (2000) 173
Kou, S., see Cheng, M. 218 (2000) 132
Kou, S., see He, J. 218 (2000) 140
Koutsopoulos, S., E. Pierri, E. Dalas, N. Tzavellas and N. Klouras, Effect of fericenium salts on the crystal growth of hydroxyapatite in aqueous solution 218 (2000) 353
Kujime, S., see Jiang, N. 218 (2000) 265
Kuroda, Y., see Miyazaki, N. 218 (2000) 221
Kuršumović, A., Y.S. Cheng, B.A. Glowacki, J. Madsen and J.E. Evetts, Study of the rate-limiting processes in liquid-phase epitaxy of thick YBaCuO films 218 (2000) 45

Lan, C.W., J.H. Chian and T.Y. Wang, Interface control mechanisms in horizontal zone-melting with slow rotation 218 (2000) 115
Lee, H. and A.J. Pearlstein, Simulation of radial solute segregation in vertical Bridgman growth of pyridine-doped benzene, a surrogate for binary organic nonlinear optical materials 218 (2000) 334
Lee, J.H., see Yoshikawa, A. 218 (2000) 67
Lee, J.H., see Koh, E. 218 (2000) 214
Lee, S.H., see Koh, E. 218 (2000) 214
Lee, T.R., see Ji, D. 218 (2000) 390
Lei Zhenlin, see Yu Zhuo 218 (2000) 245
Leszczynski, M., see Frayssinet, E. 218 (2000) 161
Li Daizong, see Yu Zhuo 218 (2000) 245
Li, M.-S., see Yin, L.-W. 218 (2000) 455
Li, W.Z., see Chen, X.H. 218 (2000) 57
Li, Y., see Sun, Z. 218 (2000) 203
Li, Y.F., X.L. Ye, B. Xu, F.Q. Liu, D. Ding, W.H. Jiang, Z.Z. Sun, Y.C. Zhang, H.Y. Liu and Z.G. Wang, Room temperature 1.55 μm emission from InAs quantum dots grown on (0 0 1)InP substrate by molecular beam epitaxy 218 (2000) 451
Li, Z.Q., see Liu, H.F. 218 (2000) 191
Liang, C.H., G.W. Meng, L.D. Zhang, N.F. Shen and X.Y. Zhang, Carbon nanotubes filled partially or completely with nickel 218 (2000) 136
Liang, J.K., see Zhang, D.Y. 218 (2000) 98
Liang Junwu, see Yu Zhuo 218 (2000) 245
Liliental-Weber, Z., see Benamara, M. 218 (2000) 447
Lin, W.X., see Zhang, D.Y. 218 (2000) 98
Little, M.E., see Ballarotto, V.W. 218 (2000) 173
Liu, F., see Sun, Z. 218 (2000) 203
Liu, F.Q., see Li, Y.F. 218 (2000) 451
Liu, G.L., see Qian, D. 218 (2000) 197
Liu, H.F., H. Chen, Z.Q. Li, L. Wan, Q. Huang, J.M. Zhou, N. Yang, K. Tao, Y.J. Han and Y. Luo, MBE growth and Raman studies of cubic and hexagonal GaN films on (0 0 1)-oriented GaAs substrates 218 (2000) 191
Liu, H.Y., see Li, Y.F. 218 (2000) 451
Liu, J.F., J.Y. Feng and J. Zhu, Growth of epitaxial $CoSi_2$ films on Si(1 0 0) substrates through direct solid phase reaction between crystalline Co films and Si substrates 218 (2000) 272
Liu, W., see Zhang, D.Y. 218 (2000) 98
Liu, X., see Zhang, H. 218 (2000) 81
Liu, Y.-X., see Yin, L.-W. 218 (2000) 455
Lobanov, S., see Isaenko, L. 218 (2000) 313
Loison, D., see Qian, D. 218 (2000) 197
Lu, Kunquar, see Chen, Xiumei 218 (2000) 93
Lu, Liwu, Yanhua Zhang, Zuntu Xu, Zhongying Xu, Zhanguo Wang, J. Wang and Weikun Ge, Effect of rapid thermal annealing on electron emission and DX centers in strained InGaAs/GaAs single quantum well laser diodes 218 (2000) 13
Luo, Y., see Liu, H.F. 218 (2000) 191

Ma, M., T. Irisawa, T. Tsuru, T. Ogawa, M. Watanabe and M. Eguchi, Study on defects in CZ-Si crystals grown by normal, cusp magnetic field and electromagnetic field techniques using multi-chroic infrared light scattering tomography 218 (2000) 232
Machajdík, D., see Španková, M. 218 (2000) 287
Madsen, J., see Kuršumović, A. 218 (2000) 45
Mahanty, S., see Wang, H.X. 218 (2000) 148

Makita, H., see Jiang, N. 218 (2000) 265
Malakhov, V., see Isaenko, L. 218 (2000) 313
Manoli, F. and E. Dalas, Spontaneous precipitation of calcium carbonate in the presence of ethanol, isopropanol and diethylene glycol 218 (2000) 359
Marín, C. and A.G. Ostrogorsky, Erratum to "Bulk growth of quasi-binary quaternary alloys". [J. Crystal Growth 211 (2000) 194–201] 218 (2000) 141
Mazur, J., see Benamara, M. 218 (2000) 447
McFadden, G.B., see Murray, B.T. 218 (2000) 434
Meng, G.W., see Liang, C.H. 218 (2000) 136
Meng, X., see Zhang, H. 218 (2000) 81
Meyler, B., see Zamir, S. 218 (2000) 181
Méziére, C., see Molas, S. 218 (2000) 399
Mimila-Arroyo, J., see Gandouzi, M. 218 (2000) 167
Miyazaki, A., see Jia, X. 218 (2000) 459
Miyazaki, N., Y. Kuroda and M. Sakaguchi, Dislocation density analyses of GaAs bulk single crystal during growth process (effects of crystal anisotropy) 218 (2000) 221
Molas, S., J. Caro, J. Santiso, A. Figueras, J. Fraxedas, C. Méziére, M. Fourmigué and P. Batail, Thin molecular films of neutral tetrathiafulvalene-derivatives 218 (2000) 399
Mori, Y.H., see Ohmura, R. 218 (2000) 372
Mühlbauer, H., see Müller, Ch. 218 (2000) 410
Müller, Ch., H. Mühlbauer, T. Steffl, B. Rellinghaus and G. Dumpich, Epitaxial growth of Fe/Pd-multilayers onto sapphire 218 (2000) 410
Muralidharan, R., see Ushasree, P.M. 218 (2000) 365
Murray, B.T., S.R. Coriell, A.A. Chernov and G.B. McFadden, The effect of oscillatory shear flow on step bunching 218 (2000) 434

Nagao, J., see Ferhat, M. 218 (2000) 250
Nakada, T., see Kaito, C. 218 (2000) 259
Nakayama, S., see Higuchi, M. 218 (2000) 282
Nguyen Thi, H., see Drevet, B. 218 (2000) 419
Nicoara, I., D. Vizman and J. Friedrich, On void engulfment in shaped sapphire crystals using 3D modelling 218 (2000) 74
Nicolov, M., Shaped single crystals of CaF_2 218 (2000) 62
Nishino, K., see Wang, H.X. 218 (2000) 148
Niu, Z.C., see Wang, X.D. 218 (2000) 209

Ogawa, T., see Ma, M. 218 (2000) 232
Ohmura, R., S. Kashiwazaki and Y.H. Mori, Measurements of clathrate-hydrate film thickness using laser interferometry 218 (2000) 372
Okumura, H., see Shen, X.Q. 218 (2000) 155
Ostrogorsky, A.G., see Marín, C. 218 (2000) 141
Ota, I., see Jiang, N. 218 (2000) 265

Park, C.S., see Koh, E. 218 (2000) 214
Park, Y.J., see Koh, E. 218 (2000) 214
Pearlstein, A.J., see Lee, H. 218 (2000) 334
Peng, J.C., see Chen, X.H. 218 (2000) 57
Péter, Á., see Polgár, K. 218 (2000) 327
Phan, M.N., see Ji, D. 218 (2000) 390
Pierri, E., see Koutsopoulos, S. 218 (2000) 353
Piper, J., see Zhang, H. 218 (2000) 81
Ploog, K.H., see Waltereit, P. 218 (2000) 143
Polgár, K., Á. Péter, I. Földvári and Zs. Szaller, Structural defects in flux-grown stoichiometric $LiNbO_3$ single crystals 218 (2000) 327
Prystawko, P., see Frayssinet, E. 218 (2000) 161

Qian, D., G.L. Liu, D. Loison, G.S. Dong and X.F. Jin, Growth and structure of Cr thin films on GaAs(001) 218 (2000) 197

Raja, S.X.J., see Thamizharasan, K. 218 (2000) 323
Ramasamy, P., see Ushasree, P.M. 218 (2000) 365
Ramsteiner, M., see Waltereit, P. 218 (2000) 143
Reiche, P., see Waltereit, P. 218 (2000) 143
Rellinghaus, B., see Müller, Ch. 218 (2000) 410

Sagayaraj, P., see Thamizharasan, K. 218 (2000) 323
Saito, Y., see Kaito, C. 218 (2000) 259
Sakaguchi, M., see Miyazaki, N. 218 (2000) 221
Sakai, S., see Wang, H.X. 218 (2000) 148
Salzman, J., see Zamir, S. 218 (2000) 181
Santiso, J., see Molas, S. 218 (2000) 399
Sarayama, S., see Aoki, M. 218 (2000) 7
Sekiguchi, T., see Aoki, M. 218 (2000) 7
Shen, H.Y., see Zhang, D.Y. 218 (2000) 98
Shen, N.F., see Liang, C.H. 218 (2000) 136
Shen, X.Q., T. Ide, S.H. Cho, M. Shimizu, S. Hara, H. Okumura, S. Sonoda and S. Shimizu, Realization of Ga-polarity GaN films in radio-frequency plasma-assisted molecular beam epitaxy 218 (2000) 155
Shimada, M., see Aoki, M. 218 (2000) 7
Shimizu, M., see Shen, X.Q. 218 (2000) 155
Shimizu, S., see Shen, X.Q. 218 (2000) 155
Shin, Y.J., see Hong, K.J. 218 (2000) 19
Shintani, Y., see Jiang, N. 218 (2000) 265
Smirnov, N.N., see Goriletsky, V.I. 218 (2000) 125
Sonoda, S., see Shen, X.Q. 218 (2000) 155
Španková, M., I. Vávra, Š. Gaži, D. Machajdík, Š. Chromik, K. Fröhlich, L. Hellemans and Š. Beňačka, Growth and recrystallization of CeO_2 thin films deposited on *R*-plane sapphire by off-axis RF sputtering 218 (2000) 287
Steffl, T., see Müller, Ch. 218 (2000) 410
Sun, L., see Zhang, H. 218 (2000) 81
Sun, Z., J. Wu, Y. Chen, F. Liu, D. Ding, Y. Li, B. Xu and Z. Wang, The effect of substrate orientation on the morphology of InAs nanostructures on (001) and (11*n*)A/B (n = 1–5) InP substrates 218 (2000) 203
Sun, Z.Z., see Li, Y.F. 218 (2000) 451

Suski, T., see Frayssinet, E. 218 (2000) 161
Swider, W., see Benamara, M. 218 (2000) 447
Szaller, Zs., see Polgár, K. 218 (2000) 327

Tao, K., see Liu, H.F. 218 (2000) 191
Tedenac, J.C., see Ferhat, M. 218 (2000) 250
Thamizharasan, K., S.X.J. Raja, F.P. Xavier and P. Sagayaraj, Growth, thermal and microhardness studies of single crystals of potassium penta borate (KB5) 218 (2000) 323
Tian, Y., see Yang, P. 218 (2000) 87
Tsuru, T., see Ma, M. 218 (2000) 232
Tzavellas, N., see Koutsopoulos, S. 218 (2000) 353

Uecker, R., see Waltereit, P. 218 (2000) 143
Ushasree, P.M., R. Muralidharan, R. Jayavel and P. Ramasamy, Growth of bis(thiourea) cadmium chloride single crystals — a potential NLO material of organometallic complex 218 (2000) 365

Vasilyeva, I., see Isaenko, L. 218 (2000) 313
Vávra, I., see Španková, M. 218 (2000) 287
Villazana, R.J., see Ji, D. 218 (2000) 390
Vizman, D., see Nicoara, I. 218 (2000) 74

Waku, Y., see Yoshikawa, A. 218 (2000) 67
Waltereit, P., O. Brandt, M. Ramsteiner, R. Uecker, P. Reiche and K.H. Ploog, Growth of *M*-plane GaN(1 $\bar{1}$ 0 0) on γ-$LiAlO_2$(1 0 0) 218 (2000) 143
Wan, L., see Liu, H.F. 218 (2000) 191
Wang, C., see Zhang, H. 218 (2000) 81
Wang, H., see Wang, X.D. 218 (2000) 209
Wang, H.X., T. Wang, S. Mahanty, F. Komatsu, T. Inaoka, K. Nishino and S. Sakai, Growth of GaN layer by metal-organic chemical vapor deposition system with a novel three-flow reactor 218 (2000) 148
Wang, J., see Lu, Liwu 218 (2000) 13
Wang, M., see Chen, X.H. 218 (2000) 57
Wang, P., see Zhang, H. 218 (2000) 81
Wang, Qiang, see Chen, Xiumei 218 (2000) 93
Wang Qiming, see Ya Zhuo 218 (2000) 245
Wang, T., see Wang, H.X. 218 (2000) 148
Wang, T.Y., see Lan, C.W. 218 (2000) 115
Wang, X.D., Z.C. Niu, H. Wang and S.L. Feng, Formation of InAs quantum dots on low-temperature GaAs epi-layer 218 (2000) 209
Wang, Z., see Sun, Z. 218 (2000) 203
Wang, Z.G., see Xu, H.Z. 218 (2000) 1
Wang, Z.G., see Li, Y.F. 218 (2000) 451
Wang, Zhanguo, see Lu, Liwu 218 (2000) 13
Washburn, J., see Benamara, M. 218 (2000) 447
Watanabe, M., see Ma, M. 218 (2000) 232
Wu, G.T., see Chen, X.H. 218 (2000) 57
Wu, J., see Sun, Z. 218 (2000) 203

Xavier, F.P., see Thamizharasan, K. 218 (2000) 323
Xu, B., see Sun, Z. 218 (2000) 203
Xu, B., see Li, Y.F. 218 (2000) 451
Xu, H.Z., Z.G. Wang, M. Kawabe, I. Harrison, B.J. Ansell and C.T. Foxon, Fabrication and characterization of metal–semiconductor–metal (MSM) ultraviolet photodetectors on undoped GaN/sapphire grown by MBE 218 (2000) 1
Xu, Zhongying, see Lu, Liwu 218 (2000) 13
Xu, Zuntu, see Lu, Liwu 218 (2000) 13

Yamane, H., see Aoki, M. 218 (2000) 7
Yang, H.S., see Chen, X.H. 218 (2000) 57
Yang, N., see Liu, H.F. 218 (2000) 191
Yang, P., P. Deng, Z. Yin and Y. Tian, The growth defects in Czochralski-grown Yb:YAG crystal 218 (2000) 87
Yang, Y., see Zhang, H. 218 (2000) 81
Yao, T., see Aoki, M. 218 (2000) 7
Ye, X.L., see Li, Y.F. 218 (2000) 451
Yelisseyev, A., see Isaenko, L. 218 (2000) 313
Yin, L.-W., Z.-D. Zou, M.-S. Li, Y.-X. Liu, Z.-Y. Hao and J.-J. Cui, Some inclusions and defects in a synthetic diamond single crystal 218 (2000) 455
Yin, Z., see Yang, P. 218 (2000) 87
Yoon, C.J., see Hong, K.J. 218 (2000) 19
Yoon, D.H., see Yoshikawa, A. 218 (2000) 67
Yoon, D.Y., see Cheong, W.S. 218 (2000) 27
Yoon, D.Y., see Hwang, N.M. 218 (2000) 33
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Yu Jinzhong, see Yu Zhuo 218 (2000) 245
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Zeng, R.R., see Zhang, D.Y. 218 (2000) 98
Zhang, D.Y., H.Y. Shen, W. Liu, W.Z. Chen, G.F. Zhang, G. Zhang, R.R. Zeng, C.H. Huang, W.X. Lin and J.K. Liang, Crystal growth, X-ray diffraction and nonlinear optical properties of Nb:$KTiOPO_4$ crystal 218 (2000) 98

Zhang, G., see Zhang, D.Y. 218 (2000) 98
Zhang, G.F., see Zhang, D.Y. 218 (2000) 98
Zhang, H., X. Meng, C. Wang, P. Wang, L. Zhu, X. Liu, C. Dong, Y. Yang, R. Cheng, J. Dawes, J. Piper, S. Zhang and L. Sun, Growth, spectroscopic properties and laser output of Er:$Ca_4YO(BO_3)_3$ and Er:Yb:$Ca_4YO(BO_3)_3$ crystals 218 (2000) 81
Zhang, L.D., see Liang, C.H. 218 (2000) 136
Zhang, S., see Zhang, H. 218 (2000) 81
Zhang, X.B., see Chen, X.H. 218 (2000) 57
Zhang, X.Y., see Liang, C.H. 218 (2000) 136
Zhang, Y.C., see Li, Y.F. 218 (2000) 451
Zhang, Yanhua, see Lu, Liwu 218 (2000) 13
Zhou, J.M., see Liu, H.F. 218 (2000) 191
Zhu, J., see Liu, J.F. 218 (2000) 272
Zhu, L., see Zhang, H. 218 (2000) 81
Zolotoyabko, E., see Zamir, S. 218 (2000) 181
Zondy, J.-J., see Isaenko, L. 218 (2000) 313
Zou, Z.-D., see Yin, L.-W. 218 (2000) 455

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Journal of Crystal Growth 218 (2000) 469–470

JOURNAL OF CRYSTAL GROWTH

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Subject index

Cellular growth
- of aluminum lithium alloys 419
- of diamond 455
Convection 74, 132, 419, 434

Dendritic growth
- of clathrate hydrate 372
Device characterization
- diodes 1
- heterojunctions 13
- quantum wells 13, 451
Diamond 265
Diodes, see Device characterization

Epitaxy, see Thin film growth

Heat flow control 294
Heterojunctions, see Device characterization
Hydrodynamics, see Convection

Kinetics
- of growth 103, 136, 245, 250, 353, 359, 434, 447
- of nucleation 103, 136, 359, 365

Lysozyme 390

Melt growth technique
- by Bridgman–Stockbarger method
- - of benzene 334
- - of copper beryllium 381
- - of lithium thioindate 313
- by Czochralski method
- - of gallium arsenide 221
- - of lithium niobate 93
- - of silicon 232, 239
- - of sodium iodide and cesium iodide 125, 277
- - of YAG 87
- - of YBCO 81
- by edge defined film fed growth
- - of calcium fluoride 62
- - of sapphire 74
- by floating zone
- - of barium boron aluminate 459
- - of praseodymium silicate 282
- - of samarium silicate 282
- by micro pulling down method
- - of oxides 67
- by zone melting
- - of succinonitril 115
Microgravity, growth under
- of aluminum lithium alloys 419

Numbers
- Marangoni 74
- Rayleigh 115

Quantum wells, see Device characterization

Solution growth technique
- by flux method
- - of gallium nitride 7
- - of lithium niobate 327
- - of potassium titanyl phosphate 98
- - of YBCO 45
- by low temperature method
- - of potassium pentaborate 323
- by recrystallization
- - of graphite 57
- by strain anneal
- - of gallium nitride 214
Stefan problem or moving boundary problem
- of succinonitril 115
Superconductivity materials, high T_c
- - of YBCO 45
Surface energy, determination
- of vaterite 359

Thin film growth, epitaxy
- by molecular beam epitaxy
- - of aluminum nitride 173
- - of chromium 197
- - of gallium arsenide 209
- - of gallium nitride 1, 143, 155, 191
- - of indium arsenide 203, 451
- - of indium gallium arsenide 13
- by vapor phase epitaxy

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00679-5

– – through metalorganic chemical vapor deposition
– – – of aluminum nitride 181
– – – of cerium oxide 287
– – – of gallium nitride 148, 161, 181, 447
– – – of iron palladium 410

Vapor growth technique
– by chemical vapor deposition
– – of diamond 40
– – of gallium arsenide 167
– – of silicon 27, 33
– by evaporation and condensation
– – of cobalt silicon 272
– – of indium sulphide 259
– – of tetrathiafulvalene 399
– by sublimation
– – of cadmium sulphide 19